

FEATURES

- Single-Chip Mixer/Oscillator and Phase-Locked Loop (PLL) Synthesizer
- Three-Band Local Oscillator
- I²C Bus Protocol (Bidirectional Data Transmission)
- 30-V Tuning Voltage Output
- Four NPN-Type Band-Switch Drivers
- Programmable Reference Divider Ratio (512, 640, or 1024)
- External 4-Pin Intermediate Frequency (IF)
 Filter Between Mixer Output and IF Amplifier
 Input
- 5-V Power Supply
- 30-Pin Thin Shrink Small-Outline Package (TSSOP)

APPLICATIONS

- TVs
- VCR/DVD Recorders
- Set-Top Boxes

DESCRIPTION

VHI OSC C **UHF RF IN** 30 VHI OSC B 29 VHF RF IN OSC GND [28 BS4 VLO OSC C 27 RF GND VLO OSC B 26 MIX OUT2 UHF OSC B1 [25 MIX OUT1 UHF OSC C1 24 IF IN2 23 UHF OSC C2 8 IF IN1 UHF OSC B2 9 22 BS2 IF GND 10 21 BS1 VCC 20 BS3 11 IF OUT ADC 12 19 CP 13 18 AS VTU 14 17 SDA **XTAL** 15 SCL 16

DBT PACKAGE

(TOP VIEW)

P0038-01

The SN761678B is a synthesized tuner IC designed for TV tuning systems. The circuit consists of a phase-locked loop (PLL) synthesizer, three-band local oscillator and mixer, 30-V output tuning amplifier, and four NPN band-switch drivers. The device is available in a small-outline package. A 15-bit programmable counter and reference divider are controlled by I²C bus protocol. Tuning step frequency is selectable by this reference divider ratio for a crystal oscillator.



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

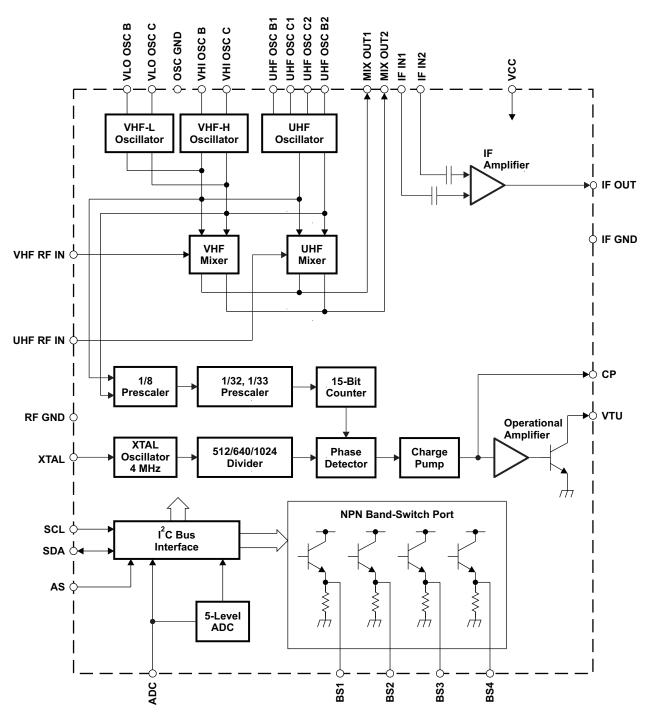
ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.



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FUNCTIONAL BLOCK DIAGRAM



B0089-02



Terminal Functions

TERMINAL		DECODINE	00050050
NAME	NO.	DESCRIPTION	SCHEMATIC
ADC	19	ADC input	Figure 1
AS	18	Address selection input	Figure 2
BS1	21	Band-switch 1 output (NPN emitter follower)	Figure 4
BS2	22	Band-switch 2 output (NPN emitter follower)	Figure 4
BS3	20	Band-switch 3 output (NPN emitter follower)	Figure 4
BS4	28	Band-switch 4 output (NPN emitter follower)	Figure 4
СР	13	Charge-pump output	Figure 5
IF GND	10	IF ground	
IF IN1	23	IF amplifier input 1	Figure 3
IF IN2	24	IF amplifier input 2	Figure 3
IF OUT	12	IF output	Figure 6
MIX OUT1	25	Mixer output 1	Figure 7
MIX OUT2	26	Mixer output 2	Figure 7
OSC GND	3	Oscillator ground	
RF GND	27	RF ground	
SCL	16	Serial clock input	Figure 8
SDA	17	Serial data input/output	Figure 9
UHF OSC B1	6	UHF oscillator base 1	Figure 10
UHF OSC B2	9	UHF oscillator base 2	Figure 10
UHF OSC C1	7	UHF oscillator collector 1	Figure 10
UHF OSC C2	8	UHF oscillator collector 2	Figure 10
UHF RF IN	30	UHF RF input	Figure 11
VCC	11	Supply voltage for mixer/oscillator/PLL: 5 V	
VHF RF IN	29	VHF RF input	Figure 12
VHI OSC B	2	VHF HIGH oscillator base	Figure 13
VHI OSC C	1	VHF HIGH oscillator collector	Figure 13
VLO OSC B	5	VHF LOW oscillator base	Figure 14
VLO OSC C	4	VHF LOW oscillator collector	Figure 14
VTU	14	Tuning voltage amplifier output	Figure 15
XTAL	15	4-MHz crystal oscillator input	Figure 16

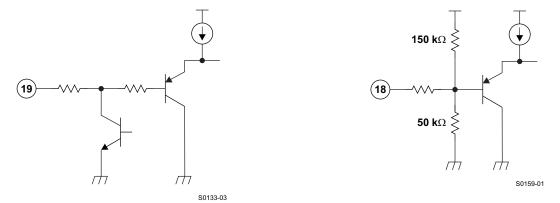
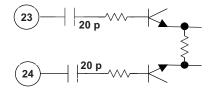


Figure 1. Figure 2.





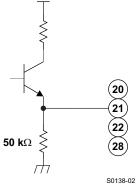


Figure 3.

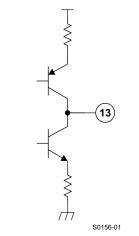


Figure 5.

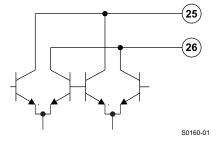


Figure 7.

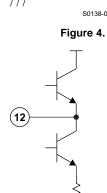


Figure 6.

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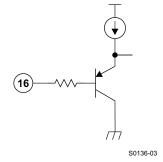
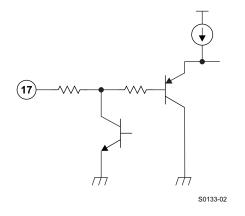


Figure 8.





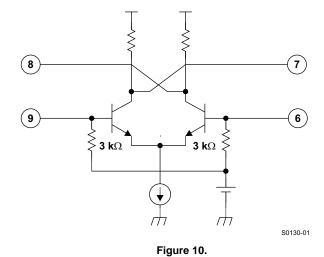
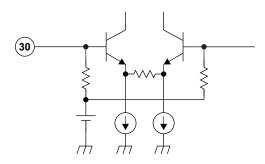
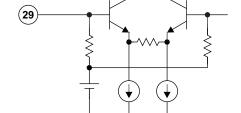


Figure 9.





S0142-05

Figure 11.

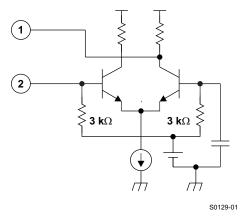


Figure 13.

Figure 12.

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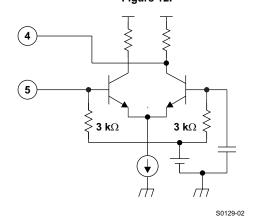


Figure 14.



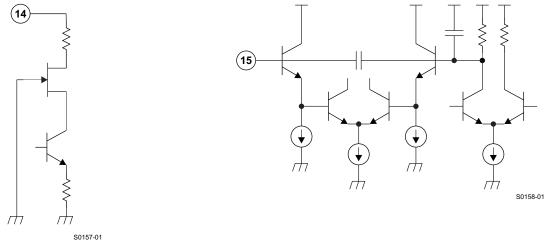


Figure 15. Figure 16.

Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

Supply voltage range, V _{CC} ⁽²⁾	VCC (pin 11)	-0.4 V to 6.5 V
Input voltage 1, V _{GND} ⁽²⁾	OSC GND, RF GND (pins 3, 27)	-0.4 V to 0.4 V
Input voltage 2, V _{VTU} ⁽²⁾	VTU (pin 14)	-0.4 V to 35 V
Input voltage 3, V _{IN} ⁽²⁾	Other pins (1, 2, 4–9, 12, 13, 15–26, 28–30)	-0.4 V to 6.5 V
Continuous total dissipation, P _D ⁽³⁾	T _A ≤ 25°C	1071 mW
Operating free-air temperature range, T _A	·	−20°C to 85°C
Storage temperature range, T _{stg}		-65°C to 150°C
Maximum junction temperature, T _J		150°C
Maximum short-circuit time, t _{SC(max)}	Each pin to V _{CC} or to GND	10 s

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating (2) Voltage values are with respect to the IF GND of the circuit.
 (3) Derating factor is 8.57 mW/°C for T_A ≥ 25°C.

Recommended Operating Conditions

		MIN	NOM	MAX	UNIT
Supply voltage, V _{CC}		4.5	5	5.5	V
Tuning supply voltage, V _{TU}			30	33	V
Output current of band switch, I _{BS}	One port on			10	mA
Operating free-air temperature, T _A		-20		85	°C



Electrical Characteristics – Total Device and Serial Interface

 $\rm V_{\rm CC} = 4.5~V$ to 5.5 V, $\rm T_{\rm A} = -20^{\circ}C$ to 85°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{CC} 1	Supply current 1			60		mA
I _{CC} 2	Supply current 2	One band switch on (I _{BS} = 10 mA)		70		mA
V_{IH}	High-level input voltage (SCL, SDA)		2.8		V_{CC}	V
V_{IL}	Low-level input voltage (SCL, SDA)				1.4	V
I _{IH}	High-level input current (SCL, SDA)				10	μΑ
I _{IL}	Low-level input current (SCL, SDA)		-10			μΑ
V_{POR}	Power-on-reset supply voltage (threshold of supply voltage between reset and operation mode)		2.1	2.8	3.6	V
I ² C Inter	face					
V _{ASH}	Address-select high-input voltage (AS)	V _{CC} = 5 V	4.5		5	V
V _{ASM1}	Address-select mid1-input voltage (AS)	V _{CC} = 5 V	2		3	V
V _{ASM2}	Address-select mid2-input voltage (AS)	V _{CC} = 5 V	1		1.5	V
V_{ASL}	Address-select low-input voltage (AS)	V _{CC} = 5 V			0.5	V
I _{ASH}	Address-select high-input current (AS)	V _{CC} = 5 V, T _A = 25°C			140	μΑ
I _{ASL}	Address-select low-input current (AS)	V _{CC} = 5 V, T _A = 25°C	-50			μΑ
V_{ADC}	ADC input voltage	See Table 8	0		V_{CC}	V
I _{ADH}	ADC high-level input current	$V_{ADC} = V_{CC}$			10	μΑ
I _{ADL}	ADC low-level input current	V _{ADC} = 0 V	-50			μΑ
V_{OL}	Low-level output voltage (SDA)	$V_{CC} = 5 \text{ V}, I_{OL} = 3 \text{ mA}$			0.4	V
I _{SDAH}	High-level output leakage current (SDA)	V _{SDA} = 5.5 V			10	μΑ
f _{SCL}	Clock frequency (SCL)			100	400	kHz
	I ² C Timing (see Figure 17)					
t _{hd(DAT)}	Data hold time		0			μs
t _(BUF)	Bus free time		1.3			μs
t _{hd(STA)}	Start hold time		0.6			μs
t _(Low)	SCL-low hold time		1.3			μs
t _(High)	SCL-high hold time		0.6			μs
t _{su(STA)}	Start setup time		0.6			μs
t _{su(DAT)}	Data setup time		0.1			μs
t _r	SCL, SDA rise time				0.3	μs
t _f	SCL, SDA fall time				0.3	μs
t _{su(STO)}	Stop setup time		0.6			μs



Electrical Characteristics – PLL and Band Switch

 $\rm V_{\rm CC} = 4.5~V$ to 5.5 V, $\rm T_{\rm A} = -20^{\circ}C$ to 85°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
N	Divider ratio	15-bit frequency word	256		32767	
f _{XTAL}	Crystal oscillator frequency	R_{XTAL} = 25 Ω to 300 Ω	3.2	4	4.48	MHz
Z _{XTAL}	Crystal oscillator input impedance		·	1.6		kΩ
V _{IXTAL2}	Minimum reference input sensitivity (XTAL)	4 MHz, ac coupling with 0.1-μF capacitor	·		100	mVp-p
V _{VTUL}	Tuning amplifier low-level output voltage	$R_L = 22 \text{ k}\Omega$, $V_{TU} = 33 \text{ V}$	·	0.4	0.5	V
I _{VTUOFF}	Tuning amplifier leakage current (off)	OS = 1, V _{TU} = 33 V	·		10	μΑ
I _{CPH}	Charge-pump high-level input current	CP = 1	·	280		μΑ
I _{CPL}	Charge-pump low-level input current	CP = 0		60		μΑ
V _{CP}	Charge-pump output voltage	PLL locked	·	1.95		V
I _{CPOFF}	Charge-pump leakage current	T2 = 0, T1 = 1, V _{CP} = 2 V, T _A = 25°C	-15		15	nA
I _{BS}	Band-switch driver output current		·		10	mA
V _{BS1}	David a vitale dei var autaut valta sa	I _{BS} = 10 mA	3			V
V _{BS2}	Band-switch driver output voltage	$I_{BS} = 10 \text{ mA}, V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C}$	3.5	3.9		V
I _{BSOFF}	Band-switch driver leakage current	V _{BS} = 0 V			3	μΑ



Electrical Characteristics - Mixer, Oscillator, IF Amplifier

 V_{CC} = 5 V, T_A = 25°C, measured in Figure 18 reference measurement circuit at 50- Ω system, IF filter characteristics: f_{peak} = 43 MHz (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
G _{c11}	Conversion gain 1 (mixer-IF amplifier),	f _{in} = 58 MHz ⁽¹⁾	22	25	28	dB	
G _{c13}	VHF-LOW	$f_{in} = 130 \text{ MHz}^{(1)}$	22	25	28	uБ	
G _{c14}	Conversion gain 1 (mixer-IF amplifier),	$f_{in} = 136 \text{ MHz}^{(1)}$	22	25	28	dB	
G _{c16}	VHF-HIGH	$f_{in} = 364 \text{ MHz}^{(1)}$	22	25	28	uБ	
G _{c17}	Conversion sein 1 (miver IF emplifier) IIIIF	$f_{in} = 804 \text{ MHz}^{(1)}$				dB	
G _{c19}	Conversion gain 1 (mixer-IF amplifier), UHF	$f_{in} = 804 \text{ MHz}^{(1)}$	25	25 28 3			
G _{c21}	Conversion gain 2 (mixer-IF amplifier),	ersion gain 2 (mixer-IF amplifier), $f_{in} = 58 \text{ MHz}^{(2)}$		16 19		dB	
G _{c23}	VHF-LOW	$f_{in} = 130 \text{ MHz}^{(2)}$	16	19	22	uБ	
G_{c24}	Conversion gain 2 (mixer-IF amplifier),	$f_{in} = 136 \text{ MHz}^{(2)}$	16	19	22	dB	
G _{c26}	VHF-HIGH	$f_{in} = 364 \text{ MHz}^{(2)}$	16	19	22	uБ	
G _{c27}	Conversion gain 2 (mixer IE amplifier) LIHE	$f_{in} = 370 \text{ MHz}^{(2)}$	20	23	26	dB	
G _{c29}	Conversion gain 2 (mixer-IF amplifier), UHF	$f_{in} = 804 \text{ MHz}^{(2)}$	19	22	25	uБ	
NF ₁	Noise figure, VHF-LOW	f _{in} = 55.25 MHz		9.5		dB	
NF ₃	Noise ligure, VHF-LOVV	f _{in} = 127.25 MHz		9.5		uБ	
NF ₄	Noise figure VAE HICH	f _{in} = 133.25 MHz		10		dB	
NF ₆	Noise figure, VHF-HIGH	f _{in} = 361.25 MHz		10		uБ	
NF ₇	Noise figure LILIE	f _{in} = 367.25 MHz		11		dB	
NF ₉	Noise figure, UHF	f _{in} = 801.25 MHz		11		uБ	
CM ₁	40/ areas and disting distantian MIF LOW	f _{in} = 55.25 MHz ⁽³⁾		89		4D. 77	
CM ₃	1% cross-modulation distortion, VHF-LOW	f _{in} = 127.25 MHz ⁽³⁾		89		dΒμV	
CM ₄	10/ grace modulation distortion \/\IE C	f _{in} = 133.25 MHz ⁽³⁾		86		4D.J/	
CM ₆	1% cross-modulation distortion, VHF-HIGH	f _{in} = 361.25 MHz ⁽³⁾		86		dΒμV	
CM ₇	10/ areas modulation distortion LUIF	$f_{in} = 367.25MHz^{(3)}$		87		4D.J/	
CM ₉	1% cross-modulation distortion, UHF	$f_{in} = 801.25 \text{ MHz}^{(3)}$	87			dΒμV	
V_{IFO1}	IF output voltage VIIF LOW	f _{in} = 55.25 MHz ⁽⁴⁾		117		dD:://	
V_{IFO3}	IF output voltage, VHF-LOW	f _{in} = 127.25 MHz ⁽⁴⁾		117		dΒμV	
V _{IFO4}	IF output voltage, VHF-HIGH	f _{in} = 133.25 MHz ⁽⁴⁾		117		dΒμV	
$V_{\rm IFO6}$	ir output voltage, vnr-nigh	$f_{in} = 361.25 \text{ MHz}^{(4)}$		117		иБμν	
$V_{\rm IFO7}$	IF output voltage IIIIF	$f_{in} = 367.25MHz^{(4)}$		117		4D: 1/	
V _{IFO9}	IF output voltage, OFF	utput voltage, UHF $f_{\text{in}} = 801.25 \text{ MHz}^{(4)}$		117		dΒμV	
$\Phi_{\sf OSC1}$	Phono poins VHE LOW	f _{in} = 55.25 MHz ⁽⁵⁾		88		dDa/LI=	
Φ_{OSC3}	Phase noise, VHF-LOW	f _{in} = 127.25 MHz ⁽⁵⁾	88			dBc/Hz	
Φ_{OSC4}	Phase poice VHE HICH	f _{in} = 133.25 MHz ⁽⁵⁾		86		dBc/Hz	
$\Phi_{\sf OSC6}$	Phase noise, VHF-HIGH	f _{in} = 361.25 MHz ⁽⁵⁾		86		ubt/fiz	
Φ_{OSC7}	Phone point LILIE	$f_{in} = 367.25MHz^{(5)}$		84		dDa/L!-	
Φ_{OSC9}	Phase noise, UHF	f _{in} = 801.25 MHz ⁽⁵⁾		84		dBc/Hz	
	Prescaler beat ⁽⁶⁾				25	dΒμV	

- (1) IF = 43 MHz, RF input level = 80 dB μ V (see Figure 19) (2) IF = 43 MHz, RF input level = 80 dB μ V (see Figure 20) (3) $f_{undes} = f_{des} \pm 6$ MHz, $P_{in} = 80$ dB μ V, AM 1 kHz, 30%, DES/CM = S/I = 46 dB (4) IF = 45.75 MHz
- (5) Offset = 10 kHz, RF input level = 70 dB μ V
- (6) Design parameter, not tested



FUNCTIONAL DESCRIPTION

I²C Bus Mode

I^2C Write Mode (R/ $\overline{W} = 0$)

Table 1. Write Data Format

	MSB							LSB	
Address byte (ADB)	1	1	0	0	0	MA1	MA0	$R/\overline{W} = 0$	A ⁽¹⁾
Divider byte 1 (DB1)	0	N14	N13	N12	N11	N10	N9	N8	A ⁽¹⁾
Divider byte 2 (DB2)	N7	N6	N5	N4	N3	N2	N1	N0	A ⁽¹⁾
Control byte (CB)	1	CP	T2	T1	T0	RSA	RSB	os	A ⁽¹⁾
Band-switch byte (BB)	Х	Х	Х	Х	BS4	BS3	BS2	BS1	A ⁽¹⁾

⁽¹⁾ A = Acknowledge

Table 2. Write Data Symbol Description

SYMBOL	DESCRIPTION	DEFAULT
MA[1:0]	Address-set bits (see Table 3)	
	Programmable counter set bits	
N[14:0]	$N = N14 \times 2^{14} + N13 \times 2^{13} + + N1 \times 2 + N0$ Oscillation frequency = $f_r \times 8 \times N$ $f_r = Reference$ frequency = 4 MHz/Reference divider	N14 = N13 = N12 = = N0 = 0
СР	Charge-pump current-set bit	CP = 1
GF .	60 μA (CP = 0), 280 μA (CP = 1)	OF = 1
T[2:0]	Test bits (see Table 4)	T[2:0] = 001
1[2.0]	Normal mode: T2 = 0, T1 = 0, T0 = 1/0	1[2.0] = 001
RSA, RSB	Reference divider ratio selection bits (see Table 5)	RSA = 0, RSB = 1
	Tuning amplifier control bit	
os	Tuning voltage on (OS = 0) Tuning voltage off, high impedance (OS = 1)	OS = 0
	Band-switch control bits	
	BSn = 0: Tr = OFF BSn = 1: Tr = ON	
	Band selection by BS1, BS2, BS4	
BS[4:1]	BS1(VL) BS2(VH) BS4(U)	BSn = 0
	1 0 0 VHF-LO	
	X 1 0 VHF-HI X X 1 UHF	
X	Don't care	



Table 3. Address Selection

MA1	MA0	VOLTAGE APPLIED ON AS INPUT
0	0	LOW: 0 V to 0.1 V _{CC}
0	1	MID2: open, or 0.2 V _{CC} to 0.3 V _{CC}
1	0	MID1: 0.4 V _{CC} to 0.6 V _{CC}
1	1	HIGH: 0.9 V _{CC} to V _{CC}

Table 4. Test Bits (1)

T2	T1	T0	DEVICE OPERATION	NOTE
0	0	0	Normal operation	
0	0	1	Normal operation	Default
0	1	X	Charge pump is off.	
1	1	0	Charge pump is sink.	
1	1	1	Charge pump is source.	
1	0	Х	Test mode	ADC not available

(1) Not used for other bit patterns

Table 5. Reference Divider Ratio

RSA	RSB	REFERENCE DIVIDER RATIO
X	0	640
0	1	1024
1	1	512

I^2C Read Mode (R/W = 1)

Table 6. Read Data Format

	MSB							LSB	
Address byte (ADB)	1	1	0	0	0	MA1	MA0	$R/\overline{W} = 1$	A ⁽¹⁾
Status byte (SB)	POR	FL	1	1	1	A2	A1	A0	1

(1) A = Acknowledge

Table 7. Read Data Symbol Description

SYMBOL	DESCRIPTION	DEFAULT
MA[1:0]	Address-set bits (see Table 3)	
POR	Power-on-reset flag	
	POR set: Power on POR reset: End-of-data transmission procedure	POR = 1
FL	In-lock flag	
	PLL locked (FL = 1), PLL unlocked (FL = 0)	
A[2:0]	Digital data of ADC (see Table 8)	



Table 8. ADC Level

A2	A1	Α0	VOLTAGE APPLIED ON ADC INPUT ⁽¹⁾			
1	0	0	0.6 V _{CC} to V _{CC}			
0	1	1	0.45 V _{CC} to 0.6 V _{CC}			
0	1	0	0.3 V _{CC} to 0.45 V _{CC}			
0	0	1	0.15 V _{CC} to 0.3 V _{CC}			
0	0	0	0 V to 0.15 V _{CC}			

(1) Accuracy is $0.03 \times V_{CC}$.

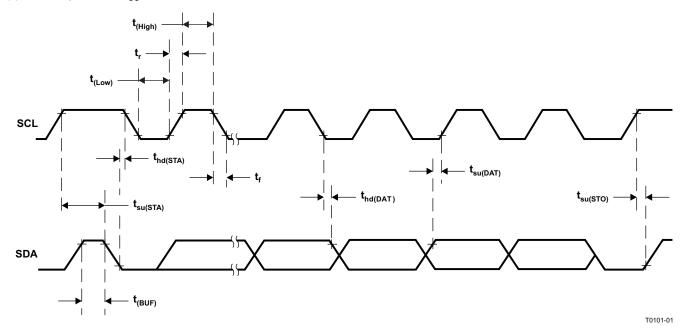
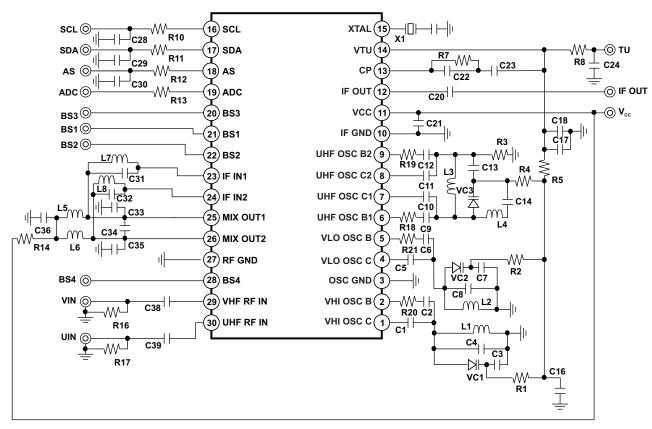


Figure 17. I²C Timing Chart



APPLICATION INFORMATION



NOTE: This application information is advisory and a performance check is required for actual application circuits. TI assumes no responsibility for the consequences of the use of this circuit, nor for any infringement of patent or patent rights of third parties that may result from its use.

Figure 18. Reference Measurement Circuit



APPLICATION INFORMATION (continued)

Component Values for Measurement Circuit

PART NAME	VALUE	PART NAME	VALUE
C1	2 p	L1	φ2.4 mm 4T 0.4 mm
C2	2 p	L2	φ3.0 mm 8T 0.32 mm
C3	82 p	L3	φ3.0 mm 2T 0.4 mm
C4	Open	L4	φ2.0 mm 3T 0.4 mm
C5	2 p	L5	φ2.4 mm 16T 0.26 mm
C6	2 p	L6	φ2.4 mm 16T 0.26 mm
C7	47 p	L7	Open
C8	3 p	L8	Open
C9	1.5 p		
C10	1 p	R1	33 k
C11	1 p	R2	33 k
C12	1.5 p	R3	22 k
C13	12 p	R4	33 k
C14	100 p	R5	22 k
C16	2.2 nF/50 V	R7	22 k
C17	2.2 n/50 V	R8	22 k
C18	2.2 n/50 V	R10	330
C20	2.2 n	R11	330
C21	4.7 n	R12	330
C22	2.2 n	R13	Short
C23	0.1 μ/50 V	R14	Short
C24	2.2 n/50 V	R16	Open
C27	68 p	R17	Open
C28	Open	R18	20
C29	Open	R19	20
C30	Open	R20	20
C31	Short		
C32	Short		
C33	Open	U1	SN761678B
C34	22 pF		
C35	Open	VC1	1T363A
C36	4.7 n	VC2	1T363A
C38	2.2 n	VC3	1T363A
C39	2.2 n		
		X1	4 MHz





APPLICATION INFORMATION (CONTINUED)

Test Circuits

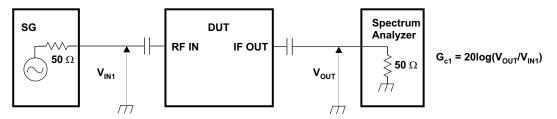


Figure 19. Measurement Circuit of Conversion Gain 1

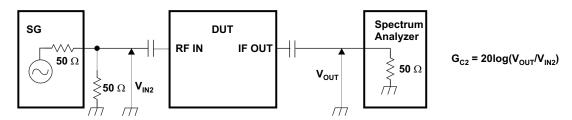


Figure 20. Measurement Circuit of Conversion Gain 2

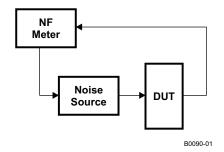


Figure 21. Noise-Figure Measurement Circuit

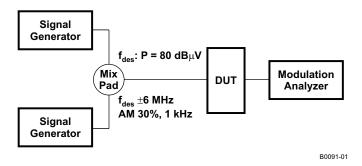


Figure 22. 1% Cross-Modulation-Distortion Measurement Circuit



TYPICAL CHARACTERISTICS

Band-Switch Driver Output Voltage (BS1-BS4)

BAND-SWITCH OUTPUT CURRENT

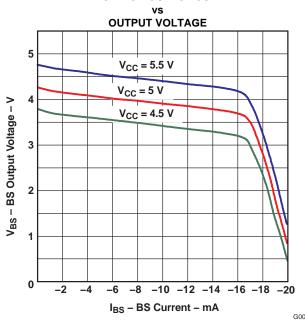


Figure 23. Band-Switch Driver Output Voltage

S-Parameter

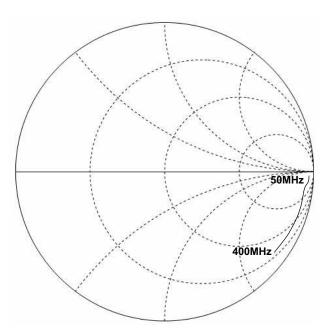


Figure 24. VHF Input

TYPICAL CHARACTERISTICS (continued)

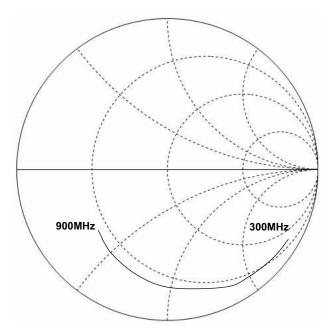


Figure 25. UHF Input

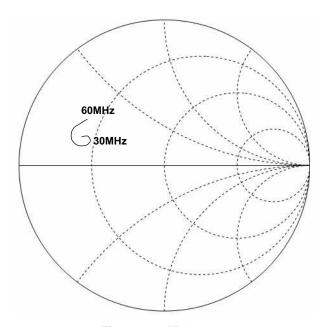


Figure 26. IF Output



PACKAGE OPTION ADDENDUM

24-Apr-2014

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins F	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
SN761678BDBTR	OBSOLETE	TSSOP	DBT	30		TBD	Call TI	Call TI	-20 to 85	B1678B	
SN761678BDCHR	OBSOLETE	TSSOP	DCH	30		TBD	Call TI	Call TI	-20 to 85	1678BDCH	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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24-Apr-2014

DBT (R-PDSO-G30)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-153.



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